

 D.G.M.E.	BTA/BTB41CW/BW	版本号: V1. 0
	双向可控硅(三项限) Triacs (3quadrants)	

产品概述 General Description

BTA/BTB41双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，三象限触发，抗干扰能力强，可靠性高。

BTA/BTB41 Triacs is fabricated using two-side diffusion processes , the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability, the Triacs series is suitable for domestic lighting , heating and motor speed controllers.

产品特点

MAIN FEATURES

- | | |
|---------------|--|
| ● 表面玻璃钝化，可靠性高 | ● Glass-Passivated Surface For Reliability |
| ● dv/dt高 | ● highly dv/dt |
| ● 通态压降低 | ● Low on-state voltage |
| ● Rohs环保产品 | ● Rohs Products |

应用领域 Applications

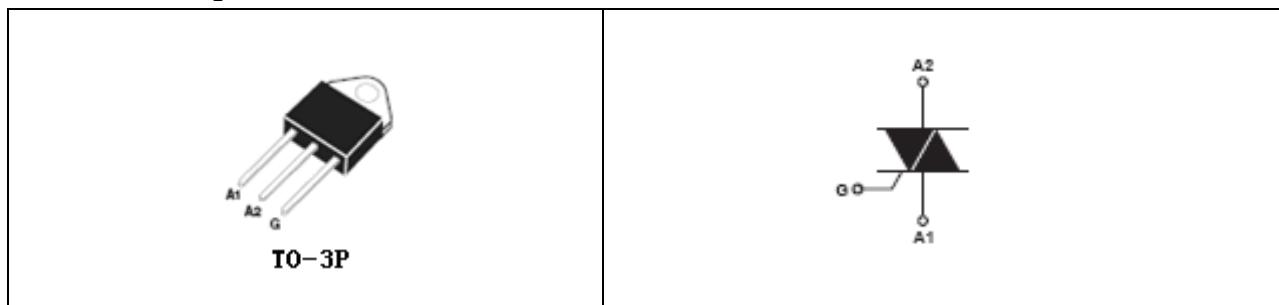
主要应用于调温控制, 调光控制, 调速控制...等。

domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I _{T (RMS)}	40	A
V _{DRM/V_{RRM}}	600	V
I _{GT}	50	mA

封装Package: T0-220



极限值(除非另有规定, Ta=25°C) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

参数 Parameter		符号 symbol	数值 Value	单位 Unit
RMS 通态电流 on-state RMS current	TO-3PI _{ns} , T _C =90°C	I _{T(RMS)}	40	A
通态峰值浪涌电流 Non repetitive surge peak on-state current	t=20ms	I _{TSM}	400	A
I ² t 耗散值 I ² t for fusing	T _P =10ms	I ² t	800	A ² s
电流上升率 Repetitive rate of rise of on-state current after triggering	F=120Hz, T _j =125°C	di/dt	50	A/μs
门极峰值电流 Peak gate current		I _{GM}	8	A
平均门极耗散功率 Average gate power		P _{G(AV)}	1.0	W
贮存结温范围 Storage temperature		T _{stg}	-40~+150	°C
工作结温范围 Operation junction temperature		T _j	-40~+125	°C

电参数(除非另有规定, Ta=25°C) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

参数名称 Parameter	符号 Symbol	测试条件 Test Conditions	规范值 Value			单位 Unit
				CW	BW	
触发电流 Gate trigger current	I _{GT}	V _D =12V, I _T =0.01A	MAX	35	50	mA
触发电压 Gate trigger voltage	V _{GT}	V _D =12V, I _T =0.01A		1.5		V
维持电流 Holding current	I _H	I _T =500mA		40	50	mA
电压上升率 Rise of off- state voltage	dv/dt	V _D =67%V _{DRM}	MIN	400	1000	V/μs
通态压降 Peak on-state voltage	V _{TM}	I _T =60A, T _P =380μs	MAX	1.55		V
断态漏电流 For Peak Repetitive ward Blocking Current	I _{DRM}	V _D =V _{DRM} , T _j =125°C	MAX	5.0		mA

热特性 THERMAL RESISTANCES

参数 Parameter	符号 symbol	数值 Value	单位 Unit
Junction to case(AC)	R _{th(j-lead)}	0.9	°C/W
Junction to ambient	R _{th(j-a)}	50	°C/W

典型特性曲线 ELECTRICAL CHARACTERISTICS(CURVES)

图1 最大耗散功率与RMS通态电流关系
 Fig.1. Maximum Power Dissipation Versus on-state current

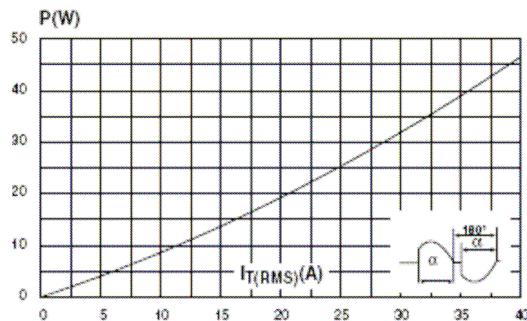


图2 平均通态电流与Tc温度关系
 Fig.2. On-state Current Versus TL

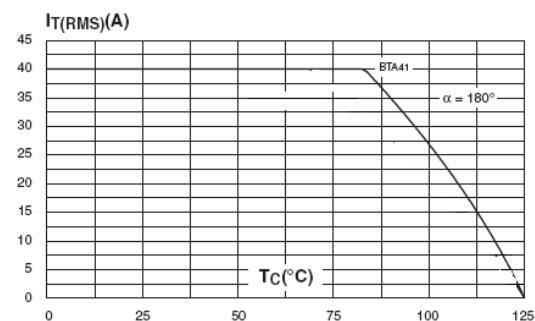


图3 通态特性
 Fig.3. On-State Characteristics

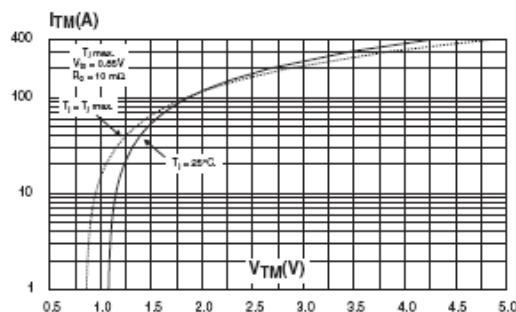


图4 通态浪涌峰值电流与周期数关系
 Fig.4. Surge Peak On-state Current Versus Number Cycles

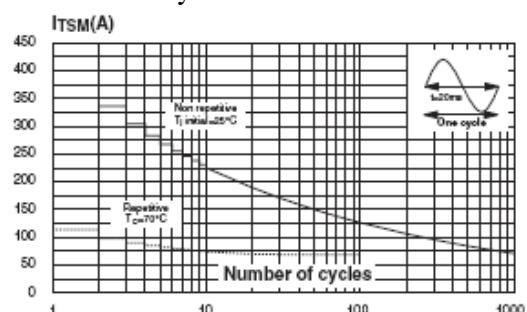
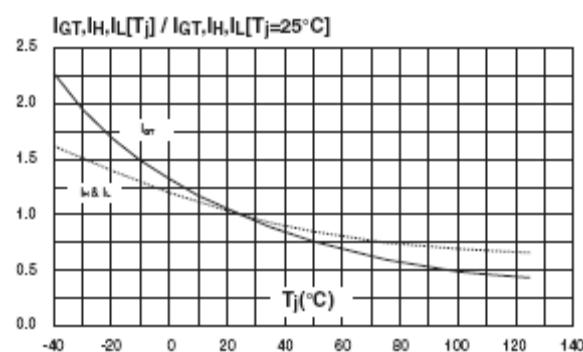
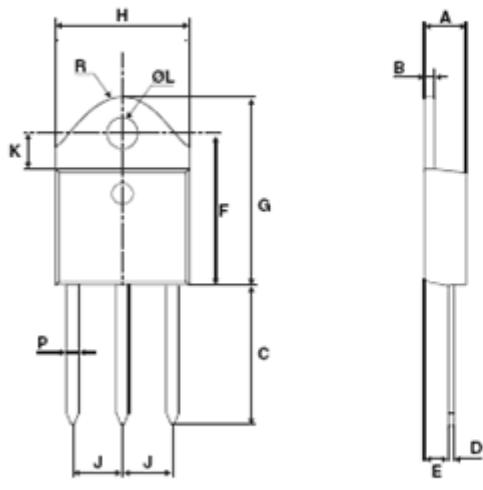


图5 I_{GT} 、 I_H 、 I_L 相对值（相对于25°C）与结温关系
 Fig.5. Relative Variation Of Gate Trigger Current
 , Holding Current And Latching Current Versus Junction Temperature (Typical Value)



TO-3P外形图 Package Mechanical Data



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.4		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
ØL	4.08		4.17	0.161		0.164
P	1.20		1.40	0.047		0.055
R		4.60			0.181	